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## IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of reclaiming silicon wafers which includes comprising:

a film removal process[[,]]; a polishing process[[,]]; and a cleaning process[[,]]; and wherein the method comprises a heating/removal process for heating the silicon wafer at 150-300.degree. C. for 20 minutes 5 hours and for removing the surface part of the silicon wafer, between the film removal process and the polishing process.

wherein the heating/removal process comprises heating the silicon wafer at 150-300 °C for 20 minutes to 5 hours and removing a surface part of the silicon wafer.

Claim 2 (Currently Amended): The method of reclaiming silicon wafers according to claim 1, wherein the heating/removal process includes comprises a mechanical removal process.

Claim 3 (Currently Amended): The method of reclaiming silicon wafers according to claim 1, wherein the heating/removal process includes comprises a chemical removal process.

Claim 4 (Original): The method of reclaiming silicon wafers according to claim 3, wherein the chemical removal process is performed using alkali hydroxides and/or alkali carbonates.

Claim 5 (Currently Amended): The method of reclaiming silicon wafers according to claim 1, wherein the method comprises both

an immersion process for comprising chemically processing the silicon wafer with a chemical processing liquid; a silicon wafer and

a the heating/removal process for comprising heating the silicon wafer at 150-300 °C for 20 minutes[[-]] to 5 hours and for removing a surface part of the silicon wafer are included between the film removal process and the polishing process.

Claim 6 (Currently Amended): The method of reclaiming silicon wafers according to claim 5, wherein a the chemical processing liquid is defined as comprises:

a hydrogen peroxide aqueous solution; a mixed solution of a hydrogen peroxide aqueous solution, an ammonia aqueous solution, and water;

a mixed solution of a hydrogen peroxide aqueous solution, hydrochloric acid, and water; alkali hydroxide aqueous solution; or

an alkali carbonate aqueous solution.

Claim 7 (Currently Amended): The method of reclaiming silicon wafers according to claim 5, wherein the heating/removal process includes comprises a mechanical removal process.

Claim 8 (Currently Amended): The method of reclaiming silicon wafers according to claim 5, wherein the heating/removal process includes comprises a chemical removal process.

Claim 9 (Original): The method of reclaiming silicon wafers according to claim 8, wherein the chemical removal process is performed using alkali hydroxides and/or alkali carbonates.

Claim 10 (Currently Amended): The method of reclaiming silicon wafers according to claim 6, wherein the heating/removal process includes comprises a mechanical removal process.

Claim 11 (Currently Amended): The method of reclaiming silicon wafers according to claim 6, wherein the heating/removal process includes comprises a chemical removal process.

Claim 12 (Original): The method of reclaiming silicon wafers according to claim 11, wherein the chemical removal is performed using alkali hydroxides and/or alkali carbonates.

Claim 13 (Original): The method of reclaiming silicon wafers according to claim 12, wherein the alkali hydroxide and/or carbonate are selected from a group consisting of potassium hydroxide, potassium carbonate, sodium hydroxide, sodium carbonate, and quaternary alkyl ammonium hydroxides.